

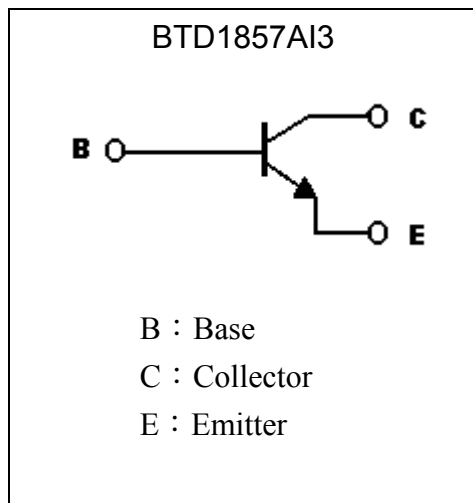
Silicon NPN Epitaxial Planar Transistor

BTD1857AI3

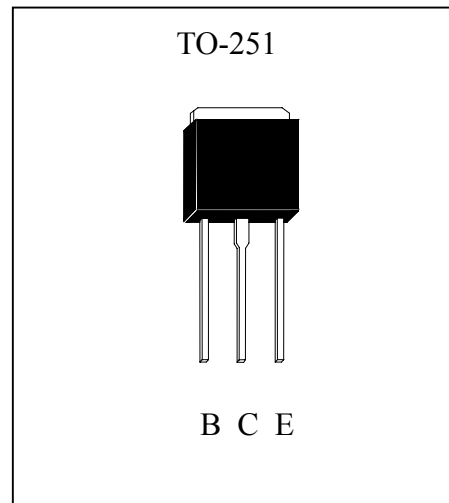
Description

- High BV_{CEO}
- High current capability
- Complementary to BTB1236AI3
- RoHS compliant package

Symbol

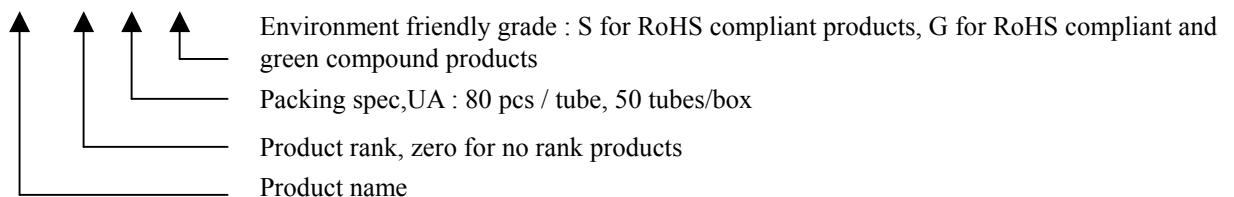


Outline



Ordering Information

Device	Package	Shipping
BTD1857AI3-0-UA-G	TO-251 (Pb-free lead plating and halogen-free package)	80 pcs/tube, 50 tubes/box



**Absolute Maximum Ratings** ($T_a=25^{\circ}\text{C}$)

Parameter	Symbol	Limits	Unit
Collector-Base Voltage	V_{CB0}	180	V
Collector-Emitter Voltage	V_{CE0}	160	V
Emitter-Base Voltage	V_{EB0}	5	V
Collector Current (DC)	I_C	1.5	A
Collector Current (Pulse)	I_{CP}	3	A
Power Dissipation @ $T_A=25^{\circ}\text{C}$	P_D	1	W
Power Dissipation @ $T_C=25^{\circ}\text{C}$		10	W
Junction Temperature	T_j	150	$^{\circ}\text{C}$
Storage Temperature	T_{stg}	-55~+150	$^{\circ}\text{C}$

Thermal Data

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-case, max	$R_{th,j-c}$	12.5	$^{\circ}\text{C}/\text{W}$
Thermal Resistance, Junction-to-ambient, max	$R_{th,j-a}$	125	$^{\circ}\text{C}/\text{W}$

Characteristics ($T_a=25^{\circ}\text{C}$)

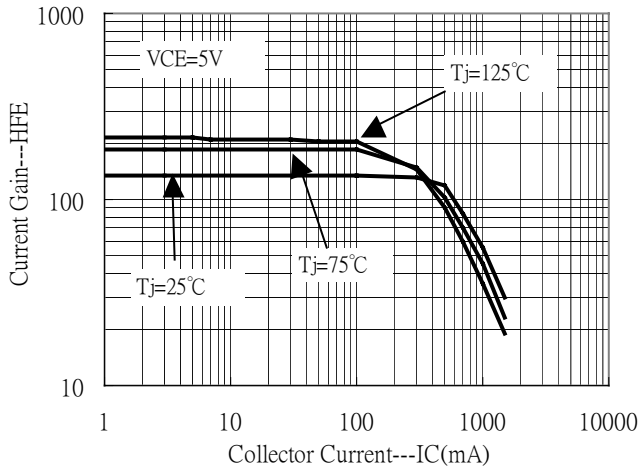
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV_{CB0}	180	-	-	V	$I_C=50\mu\text{A}$, $I_E=0$
BV_{CE0}	160	-	-	V	$I_C=1\text{mA}$, $I_B=0$
BV_{EB0}	5	-	-	V	$I_E=50\mu\text{A}$, $I_C=0$
I_{CB0}	-	-	1	μA	$V_{CB}=160\text{V}$, $I_E=0$
I_{EB0}	-	-	1	μA	$V_{EB}=4\text{V}$, $I_C=0$
* $V_{CE(saf)}$	-	-	0.6	V	$I_C=1\text{A}$, $I_B=100\text{mA}$
* $V_{BE(on)}$	-	-	1.5	V	$V_{CE}=5\text{V}$, $I_C=150\text{mA}$
h_{FE1}	180	-	390	-	$V_{CE}=5\text{V}$, $I_C=150\text{mA}$
h_{FE2}	80	-	-	-	$V_{CE}=5\text{V}$, $I_C=500\text{mA}$
f_T	-	200	-	MHz	$V_{CE}=5\text{V}$, $I_C=150\text{mA}$
C_{ob}	-	13	-	pF	$V_{CB}=10\text{V}$, $I_E=0$, $f=1\text{MHz}$

*Pulse Test: Pulse Width $\leq 380\mu\text{s}$, Duty Cycle $\leq 2\%$

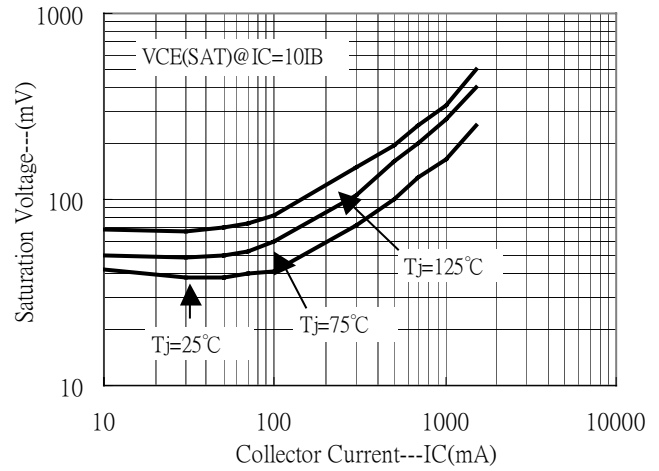


Typical Characteristics

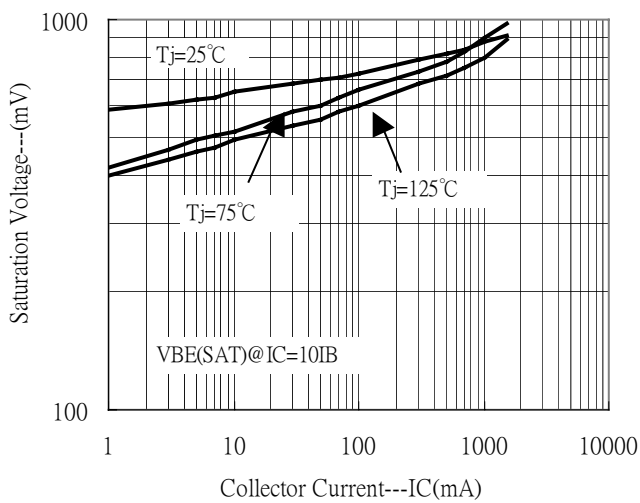
Current Gain vs Collector Current



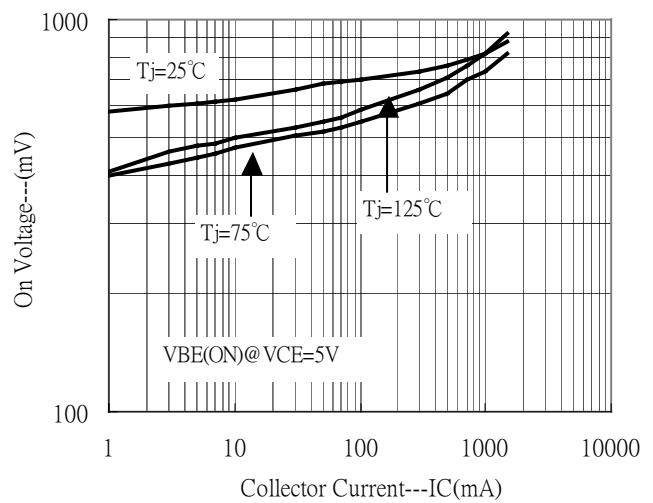
Saturation Voltage vs Collector Current



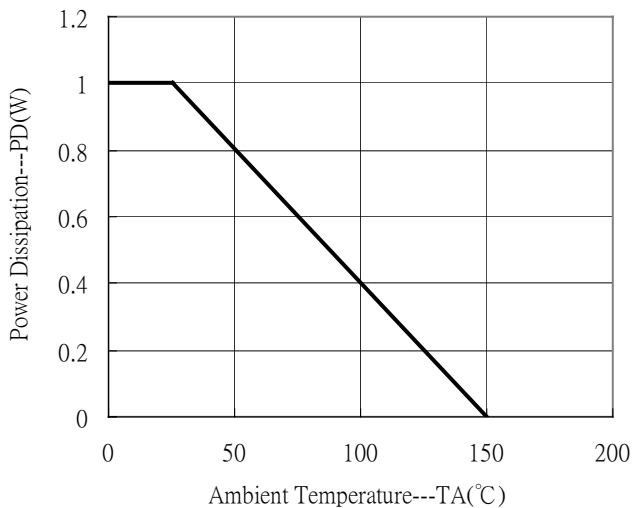
Saturation Voltage vs Collector Current



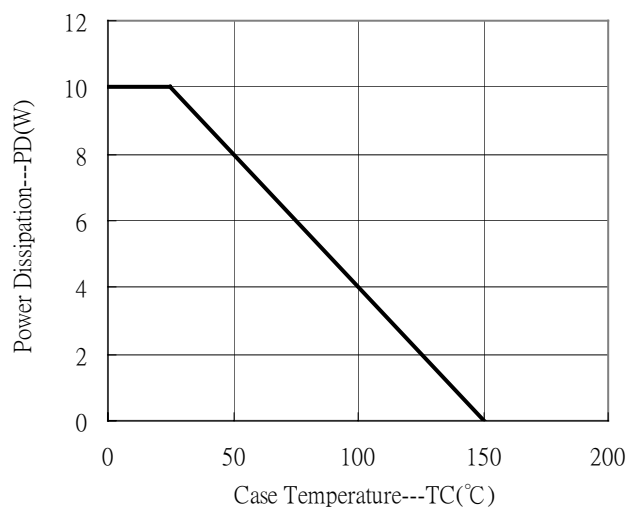
On Voltage vs Collector Current



Power Derating Curve



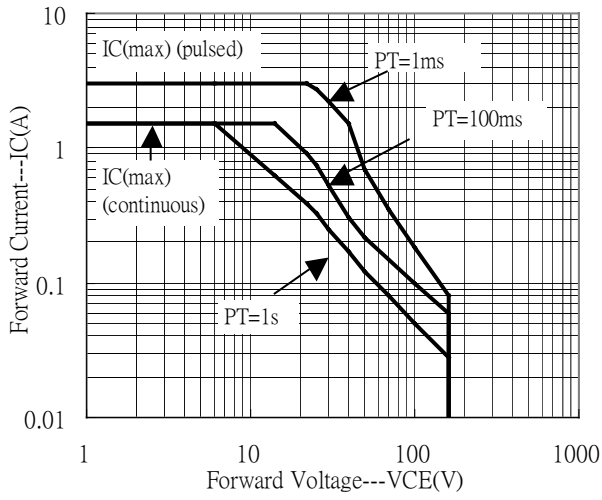
Power Derating Curve





Typical Characteristics(Cont.)

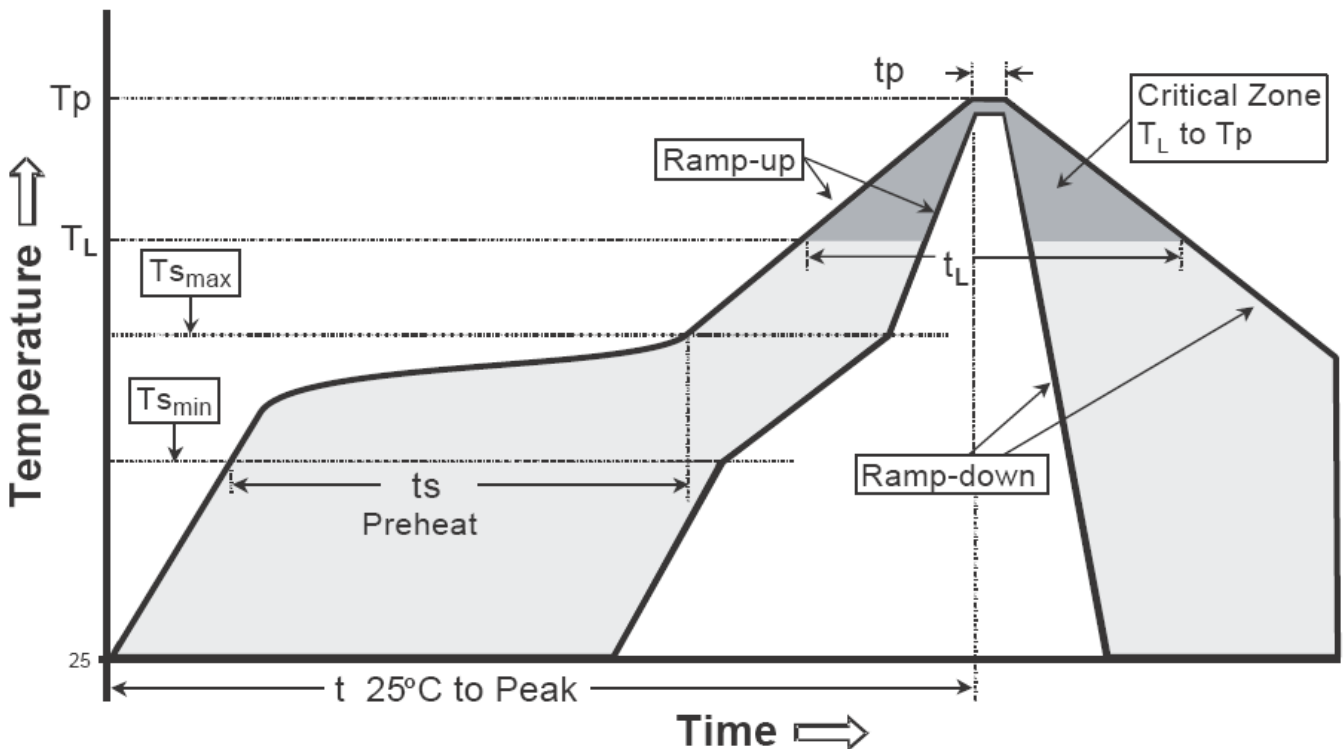
Safe Operating Area



Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

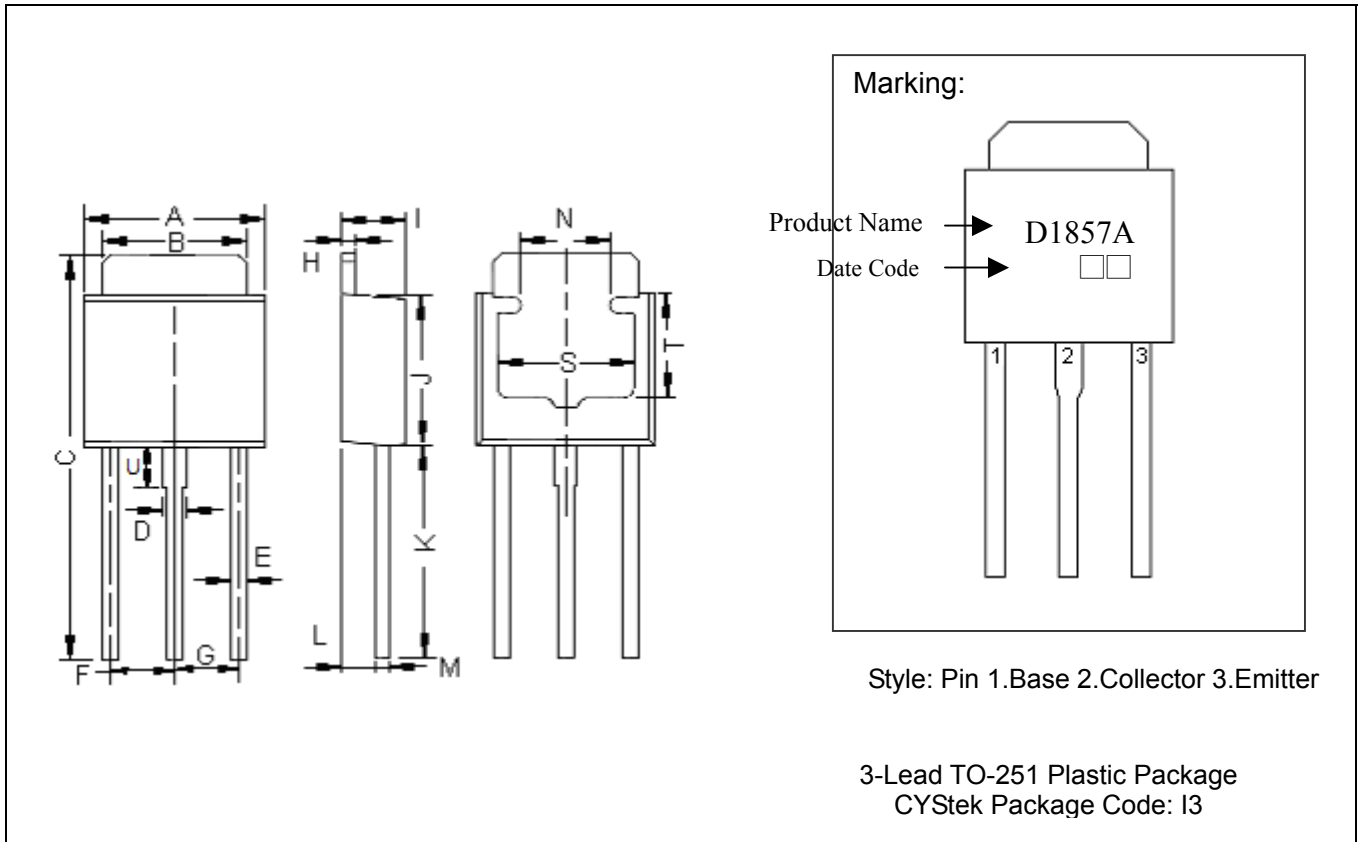
Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (T _{smax} to T _p)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(T _{s min})	100°C	150°C
-Temperature Max(T _{s max})	150°C	200°C
-Time(t _{s min} to t _{s max})	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (T _L)	183°C	217°C
- Time (t _L)	60-150 seconds	60-150 seconds
Peak Temperature(T _p)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

TO-251 Dimension



DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.250	0.262	6.350	6.650	J	0.213	0.224	5.400	5.700
B	0.205	0.213	5.200	5.400	K	0.295	0.311	7.500	7.900
C	0.571	0.587	14.500	14.900	L	0.042	0.054	1.050	1.350
D	0.028	0.035	0.700	0.900	M	0.017	0.023	0.430	0.580
E	0.020	0.028	0.500	0.700	N	0.118	REF	3.000	REF
F	0.091 TYP		2.300 TYP		S	0.197	REF	5.000	REF
G	0.091 TYP		2.300 TYP		T	0.150	REF	3.800	REF
H	0.017	0.023	0.430	0.580	U	0.055	REF	1.400	REF
I	0.087	0.094	2.200	2.400					

Notes: 1.Controlling dimension: millimeters.
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead: Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

Important Notice:

- All rights are reserved. Reproduction in whole or in part is prohibited without the prior written approval of CYStek.
- CYStek reserves the right to make changes to its products without notice.
- CYStek **semiconductor products are not warranted to be suitable for use in Life-Support Applications, or systems.**
- CYStek assumes no liability for any consequence of customer product design, infringement of patents, or application assistance.